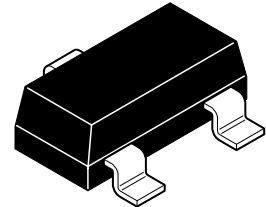


ZXTN25060BFH

60V, SOT23, NPN medium power transistor

Summary

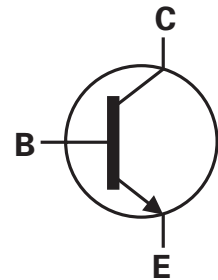
$BV_{CEX} > 150V$
 $BV_{CEO} > 60V$
 $BV_{ECO} > 6V$
 $I_{C(cont)} = 3.5A$
 $V_{CE(sat)} < 65\text{ mV @ } 1A$
 $R_{CE(sat)} = 43\text{ m}\Omega$
 $P_D = 1.25W$



Complementary part number ZXTP25060BFH

Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

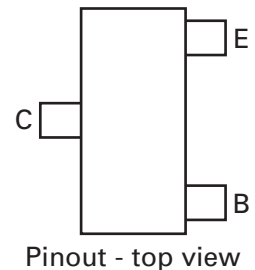


Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 150V forward blocking voltage

Applications

- Lamp, relay and solenoid drivers
- General switching in automotive and industrial applications
- Motor drive and control



Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25060BFHTA	7	8	3,000

Device marking

019

ZXTN25060BFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	150	V
Collector-emitter voltage (forward blocking)	V_{CEX}	150	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	6	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current ^(b)	I_C	3.5	A
Peak pulse current	I_{CM}	10	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a) Linear derating factor	P_D	0.73 5.84	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b) Linear derating factor	P_D	1.05 8.4	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c) Linear derating factor	P_D	1.25 9.6	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d) Linear derating factor	P_D	1.81 14.5	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

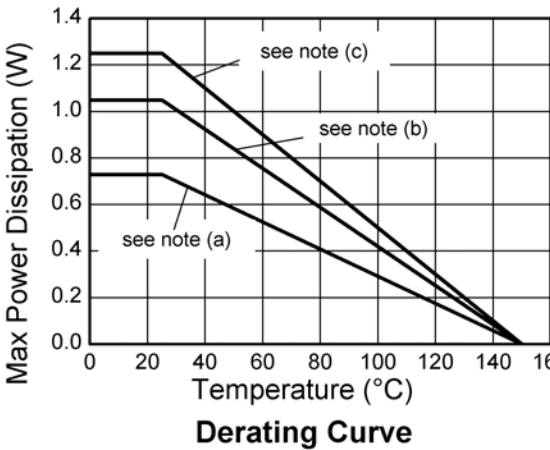
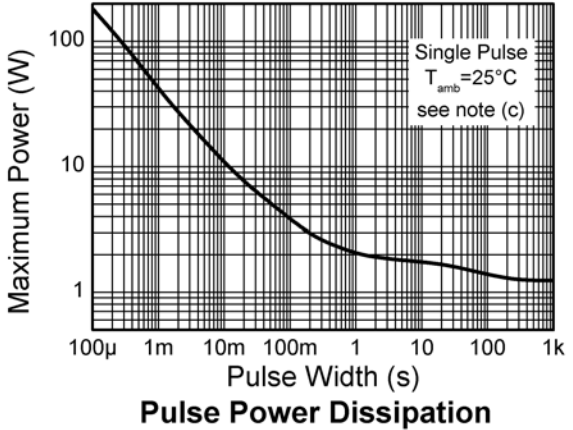
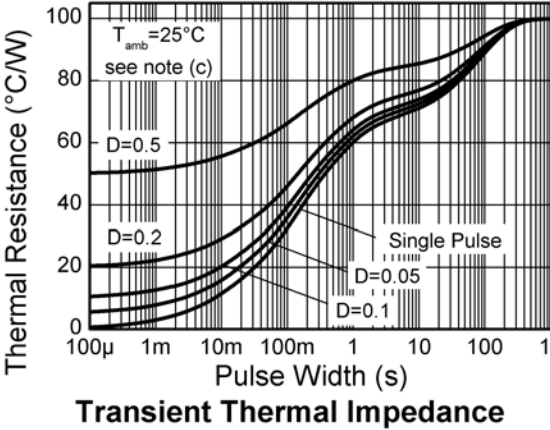
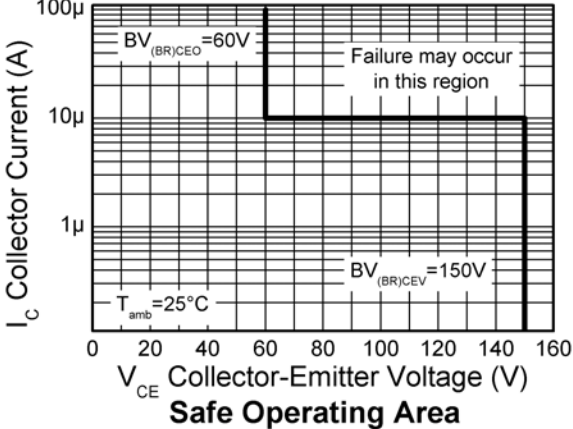
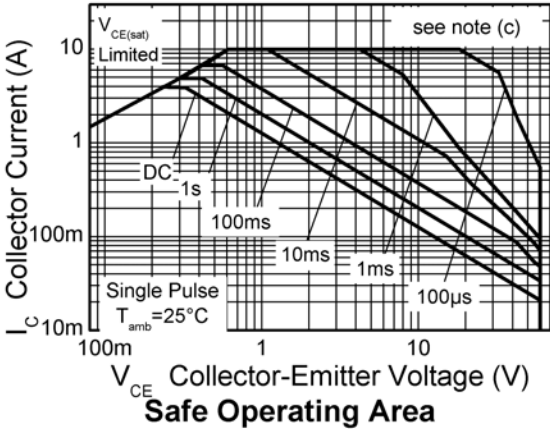
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

ZXTN25060BFH

Characteristics



ZXTN25060BFH

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

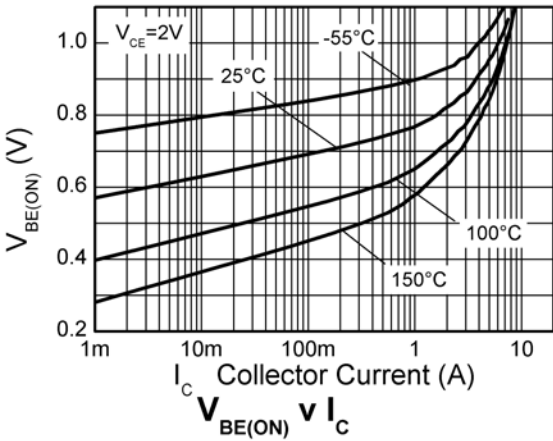
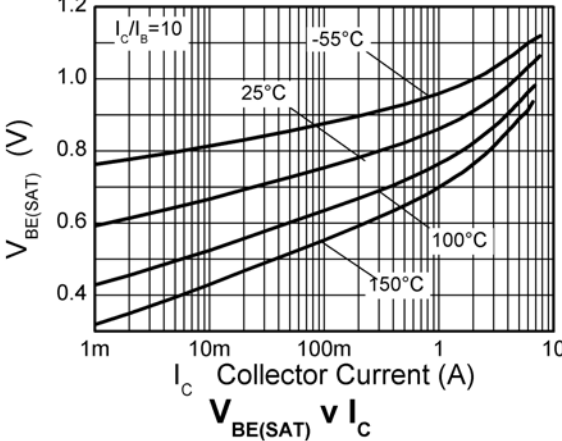
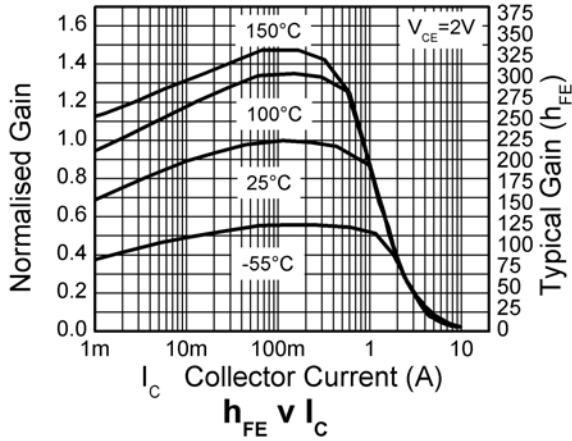
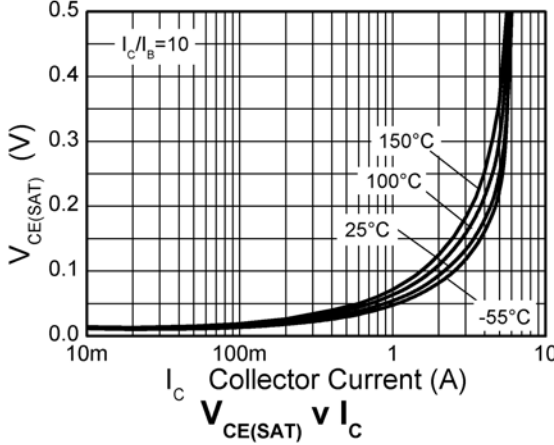
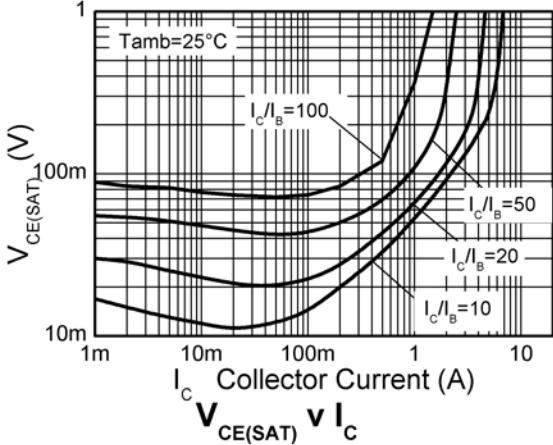
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	150	190		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	150	190			$I_C = 100\mu\text{A}$, $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	60	80		V	$I_C = 10\text{mA}$ (*)
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	8		V	$I_E = 100\mu\text{A}$, $R_{BC} \leq 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	6	7		V	$I_E = 100\mu\text{A}$,
Emitter-base breakdown voltage	BV_{EBO}	7	8		V	$I_E = 100\mu\text{A}$
Collector cut-off current	I_{CBO}		<1	50 20	nA μA	$V_{CB} = 120\text{V}$ $V_{CB} = 120\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	I_{CEX}		-	100	nA	$V_{CE} = 120\text{V}$; $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter cut-off current	I_{EBO}		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		33	40	mV	$I_C = 0.5\text{A}$, $I_B = 50\text{mA}$ (*)
			73	95	mV	$I_C = 0.5\text{A}$, $I_B = 10\text{mA}$ (*)
			50	65	mV	$I_C = 1\text{A}$, $I_B = 100\text{mA}$ (*)
			150	175	mV	$I_C = 3.5\text{A}$, $I_B = 350\text{mA}$ (*)
Base-emitter saturation voltage	$V_{BE(sat)}$		960	1050	mV	$I_C = 3.5\text{A}$, $I_B = 350\text{mA}$ (*)
Base-emitter turn-on voltage	$V_{BE(on)}$		865	950	mV	$I_C = 3.5\text{A}$, $V_{CE} = 2\text{V}$ (*)
Static forward current transfer ratio	h_{FE}	100	200	300		$I_C = 10\text{mA}$, $V_{CE} = 2\text{V}$ (*)
		90	180			$I_C = 1\text{A}$, $V_{CE} = 2\text{V}$ (*)
		25	40			$I_C = 3.5\text{A}$, $V_{CE} = 2\text{V}$ (*)
Transition frequency	f_T		185		MHz	$I_C = 100\text{mA}$, $V_{CE} = 5\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		11.5	20	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$ (*)
Turn-on time	$t_{(on)}$		34		ns	$V_{CC} = 10\text{V}$. $I_C = 500\text{mA}$,
Turn-off time	$t_{(off)}$		566		ns	$I_{B1} = I_{B2} = 50\text{mA}$.

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

ZXTN25060BFH

Typical characteristics



ZXTN25060BFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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